Full list of publications by Kevin J. Chen

Book Chapters


Refereed journal papers


91. X. Liu, C. Zhan, K. W. Chan, W. Liu, L. S. Tan, K. J. Chen, and Y. -C. Yeo, “AlGaN/GaN-on-Si metal-oxide-semiconductor high-electron-mobility transistor with breakdown voltage of 800 V and On-state resistance of 3 mohm cm2 using a


158. Z. Cheng, Y. Cai, J. Liu, Y. G. Zhou, K. M. Lau, and K. J. Chen, "A Low Phase-Noise X-Band MMIC VCO Using High-Linearity and Low-Noise Composite-Channel Al0.3Ga0.7N/Al0.05Ga0.95N/GaN HEMTs", *IEEE Trans. Microwave Theory and Techniques*, vol. 55, No. 1, pp. 23-29, Jan 2007.


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10. M. Hua, Q. Qian, J. Wei, Z. Zhang, G. Tang, and K. J. Chen, "TDDB and PBTI Characterizations of Fully-recessed E-mode GaN MIS-FETs with LPCVD-SiNx/PECVD-SiNx Gate Dielectric Stack," *2017 International Conference*


31. M. Hua, C. Liu, S. Yang, S. Liu, K. Fu, Z. Dong, Y. Cai, B. Zhang, and K. J. Chen, "Gate Leakage and Time-Dependent Dielectric Breakdown Characteristics of
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34. S. Liu, S. Yang, C. Liu, Y. Lu and K. J. Chen, "High-Performance Gate-Recessed Normally-Off GaN MIS-HEMTs with Thin Barrier Layer," 11th Int. Conf. on Nitride Semiconductors (ICNS-11), Beijing, China, Aug. 30- Sept. 4, 2015.


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73. Z. Tang, S. Huang, Q. Jiang, S Liu, C. Liu, and K. J. Chen, “600V 1.3mΩ·cm² Low-Leakage Low-Current-Collapse AlGaN/GaN HEMTs with AlN/SiNx


79. (Invited talk) S. Yang, S. Huang, Q. Zhao, and K. J. Chen, “Enhancement-mode AlGaN/GaN MISHEMTs with fluorinated high-


182. B. P. Yan, E. S. Yang, Y. F. Yang, X. Q. Wang, K. K. P. Tsui, and K. J. Chen,"RF Large Signal Characterization of InGaP/GaAs Power Heterostructure-emitter Bipolar


